

the single crystalline film is formed from one of the group of Si, GaN, GaAs, $\text{Ga}_{1-x}\text{Al}_x\text{As}$, ZnSe, ZnS, CdTe, $\text{ZnS}_{1-x}\text{Se}_x$, and YBCO.

22. The method of claim 18, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, SrTiO_3 , and sapphire; and

the single crystalline film is formed from one of the group of Si, GaAs, $\text{Ga}_{1-x}\text{Al}_x\text{As}$, ZnSe, ZnS, CdTe, $\text{ZnS}_{1-x}\text{Se}_x$, and YBCO.

23. The method of claim 18 wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, and SrTiO_3 ; and

the single crystalline film is formed from one of the group of Si, GaN, GaAs, $\text{Ga}_{1-x}\text{Al}_x\text{As}$, ZnSe, ZnS, CdTe, $\text{ZnS}_{1-x}\text{Se}_x$, and YBCO.--